

Analog Semiconductor IC

VDD Series

Low voltage, Low power, $\pm 1\%$ High detect accuracy
CMOS Voltage Detector with Delay circuit

(IMPORTANT: Please check the last page for Genuine Product Labeling)

Rev. E13-01

Website: www.anasemi.com
Tel: +852-3590-8442
Email: sales@anasemi.com



AnaSem

Products Data Sheet

Analog Semiconductor IC

Low voltage, Low power, $\pm 1\%$ High detect accuracy with delay circuit CMOS Voltage Detector

VDD Series

GENERAL DESCRIPTIONS

The VDD series are delay circuit built-in voltage detectors with low voltage, low power consumption and high accuracy. The accuracy of the detection voltage is detected based on a voltage reference of high accuracy that the temperature coefficient is controlled. The detection voltage is made in high accuracy by using the laser trimming technology. Because the delay circuit is built-in, delay time can be set without any external components.



RoHS
COMPLIANCE

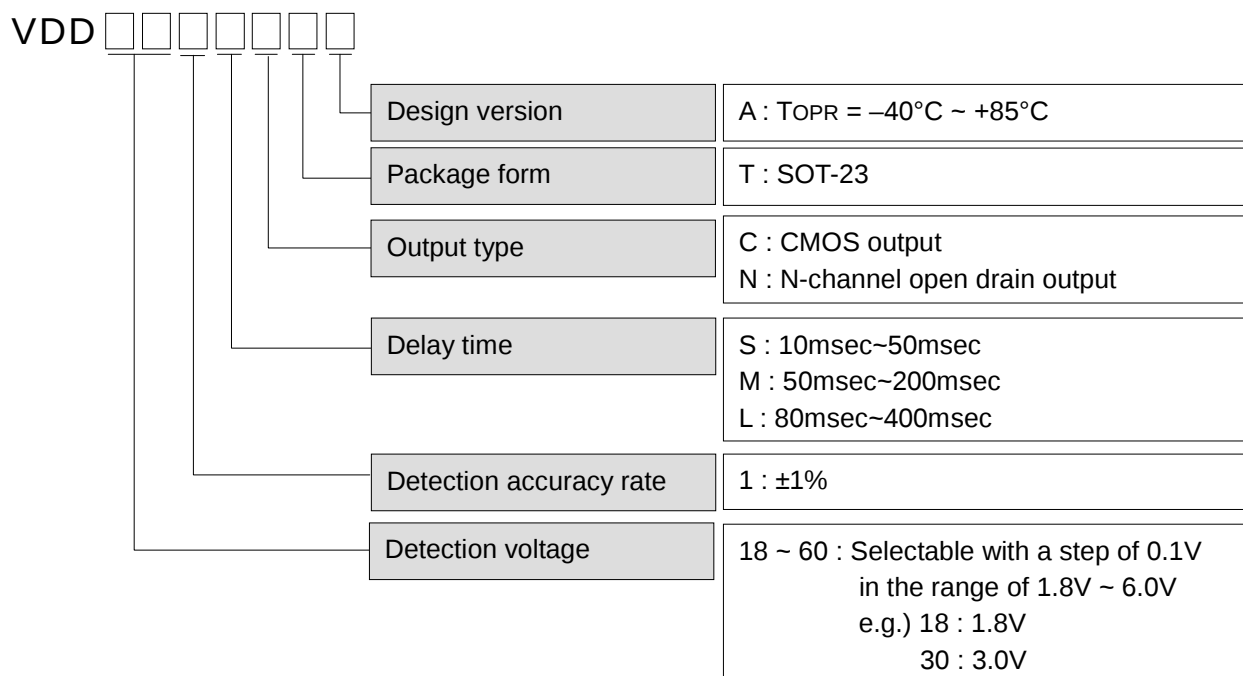
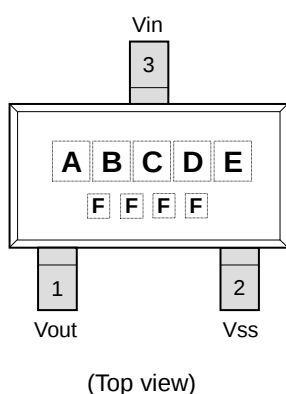


FEATURES

- Detection voltage range 1.8V~6.0V (selectable with a step of 0.1V)
- Operating voltage range 0.7V~6.0V
- High accuracy detection voltage $\pm 1\%$ ($V_{DET}=1.8V\sim 6.0V$)
- Detection voltage temperature characteristics Typ. $\pm 20\text{ppm}/^\circ\text{C}$ ($V_{DET}=1.8V\sim 6.0V$)
- Delay time S/10~50ms, M/50~200ms, L/80~400ms
- Output types CMOS or N-channel open drain
- Low current consumption Typ. $0.6\mu\text{A}$ ($V_{IN}=1.5V$)
- Operating temperature range $-40^\circ\text{C} \sim +85^\circ\text{C}$
- Small package SOT-23 (2.9×2.8×1.1mm)

APPLICATIONS

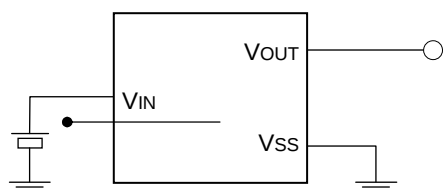
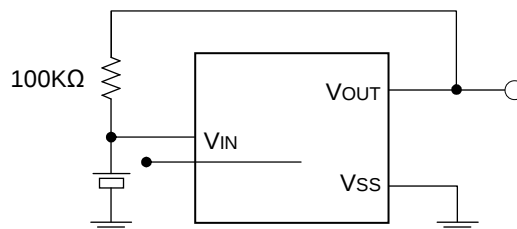
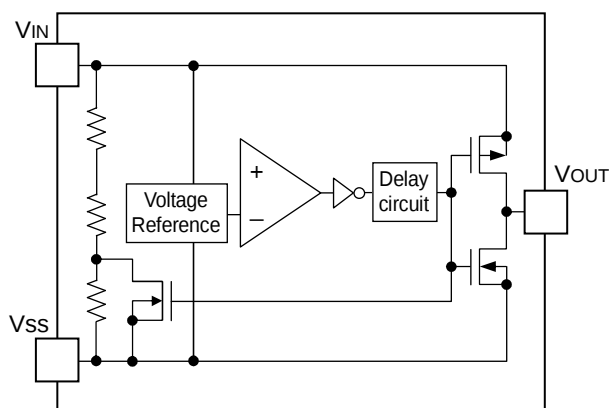
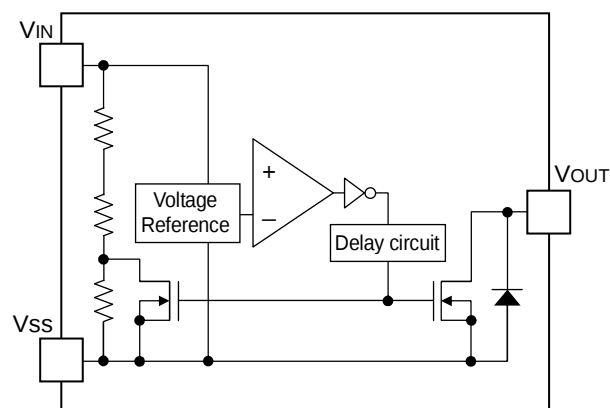
- Reset of microprocessor
- Power-on reset of system
- Charge detection of battery
- Battery back-up of memory
- Monitoring of battery life time
- Delay circuit

PRODUCTS NUMBERING GUIDE**PIN CONFIGURATION / MARKING SPECIFICATION (SOT-23)**● **Pin Configuration**

No.	Symbol	Descriptions
1	VOUT	Output
2	VSS	Power ground
3	VIN	Voltage input

● **Marking Specification**

Code	Mark	Contents
A	C or N	Output type
BC	18~60	Detection voltage
D	S, M or L	Delay time
E	A	Version
F	Internal rule	Lot number

TYPICAL APPLICATION CIRCUITS● **CMOS output**● **N-channel open drain output****BLOCK DIAGRAM**● **CMOS output**● **N-channel open drain output****ABSOLUTE MAXIMUM RATINGS**

Items		Symbol	Ratings	Unit
Input voltage range		V _{IN}	-0.3 ~ +7.0	V
Output current		I _{OUT}	50	mA
Output voltage range		V _{OUT}	V _{SS} -0.3 ~ V _{IN} +0.3	V
Power dissipation ※1)	SOT-23	P _D	400	mW
Operating temperature range		T _{OPR}	-40 ~ +85	°C
Storage temperature range		T _{STG}	-55 ~ +125	°C

Note :

※1) Power dissipation depends on conditions of mounting on boards.

PCB dimension is 50mm×50mm×1.6mm.

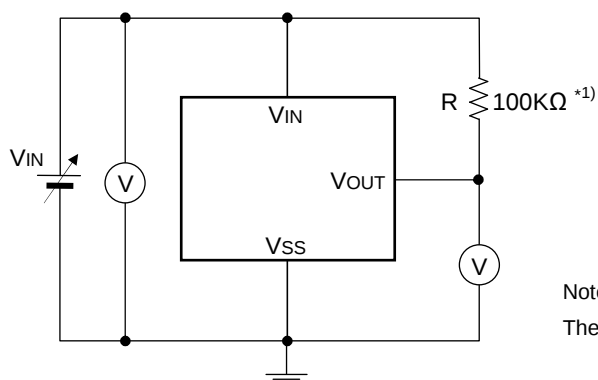
ELECTRICAL CHARACTERISTICS

(Ta=25°C unless otherwise specified)

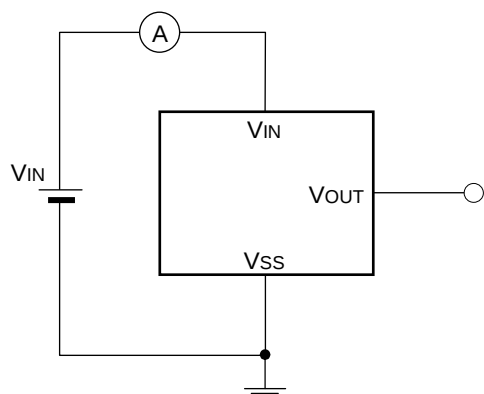
Items	Symbol	Conditions		Min.	Typ.	Max.	Unit	Test circuit
Operating voltage	V _{IN}	V _{DET} = 1.8V ~ 6.0V		0.7	-	6.0	V	1
Detection voltage	V _{DET}	V _{DET} = 1.8V ~ 6.0V Ta = -40°C ~ +85°C		V _{DET} ×0.99	V _{DET}	V _{DET} ×1.01	V	1
Hysteresis range	V _{HYS}			V _{DET} ×0.02	V _{DET} ×0.05	V _{DET} ×0.08	V	1
Output current	I _{OUT}	N-ch V _{DS} =0.5V	V _{IN} =0.7V	0.1	0.4	-	mA	3
			V _{IN} =1.0V	1.0	2.3	-	mA	
			V _{IN} =2.0V	3.0	8.2	-	mA	
			V _{IN} =3.0V	5.0	11.1	-	mA	
			V _{IN} =4.0V	6.0	12.8	-	mA	
			V _{IN} =5.0V	7.0	13.8	-	mA	
		CMOS P-ch V _{DS} =2.1V	V _{IN} =6.0V	-	-9.5	-1.5	mA	4
		CMOS N-ch V _{DS} =2.1V	V _{IN} =6.0V	1.5	9.5	-	mA	3
Current consumption	I _{SS}		V _{IN} =1.5V	-	0.6	2.1	μA	2
			V _{IN} =2.0V	-	0.7	2.5	μA	
			V _{IN} =3.0V	-	0.8	2.8	μA	
			V _{IN} =4.0V	-	0.9	3.0	μA	
			V _{IN} =5.0V	-	1.0	3.4	μA	
Leak current	I _{LEAK}	V _{IN} =6.0V V _{OUT} =6.0V		-	10	100	nA	3
Detection voltage temperature coefficient	$\frac{\Delta V_{DET}}{\Delta Ta \cdot V_{DET}}$	V _{DET} = 1.8V ~ 6.0V Ta = -40°C ~ +85°C		-	±20	-	ppm/°C	1
Delay time V _{REL} →V _{OUT} inversion	T _{DLY}	V _{IN} = 0.7V ~ 6.0V		10	-	50	ms	5
				50	-	200	ms	
				80	-	400	ms	

TEST CIRCUITS

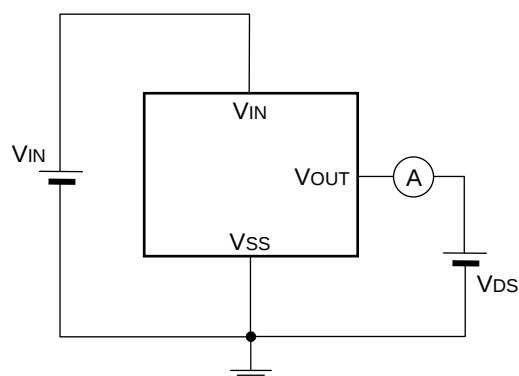
- **Circuit (1)** – Operating voltage, Detection voltage, Hysteresis range, Detection voltage temperature coefficient



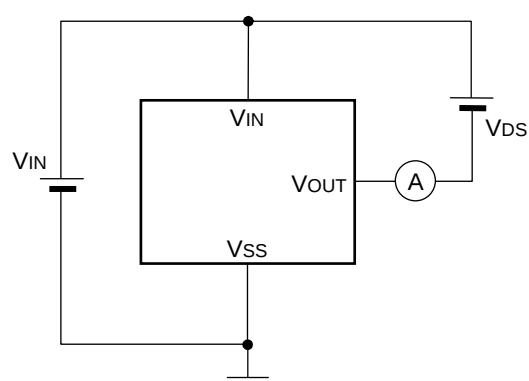
- **Circuit (2)** – Current consumption



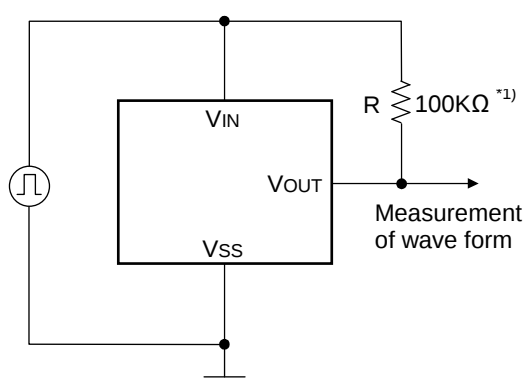
- **Circuit (3)** – N-ch driver output current



- **Circuit (4)** – P-ch driver output current



- **Circuit (5)** – Delay time ($V_{REL} \rightarrow V_{OUT}$ inversion)

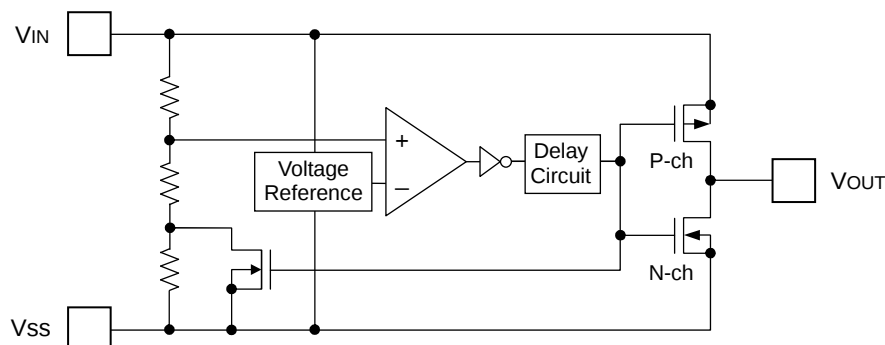


Note 1) :
The resistor (100kΩ) is not necessary for CMOS output products.

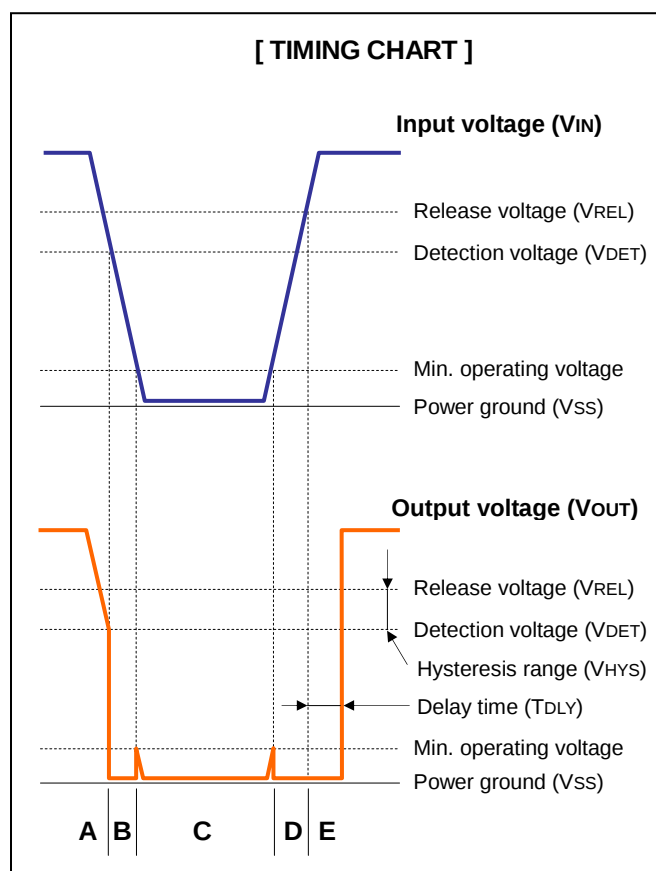
DESCRIPTION OF OPERATION

● General operation (CMOS Output)

In reference to following the block diagram of CMOS output VDD series ;

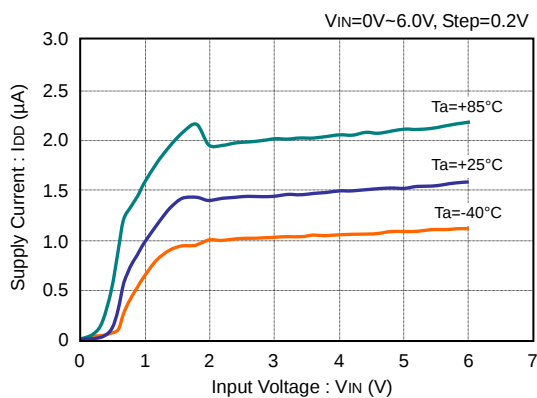


- A. When the input voltage (V_{IN}) is higher than the release voltage (V_{REL}), the input voltage (V_{IN}) is provided at the output terminal because N-ch transistor is OFF and the P-ch transistor is ON. And, the output maintains the same level of input as long as the input voltage remains above the detection voltage (V_{DET}).
- B. When the input voltage (V_{IN}) falls below the detection voltage (V_{DET}), the N-ch transistor is ON and the P-ch transistor is OFF. And, the output voltage (V_{OUT}) is same as ground level (V_{SS}).
- C. When the input voltage (V_{IN}) falls below the min. operating voltage, the output becomes unstable, or goes to V_{IN} when the output is pulled up to V_{IN} .
- D. When the input voltage (V_{IN}) rises above the minimum voltage, the ground voltage (V_{SS}) level is maintained even though the input voltage (V_{IN}) rises above the detection voltage (V_{DET}) as long as it does not exceed the release voltage (V_{REL}) level.
- E. Following delay time, the N-ch transistor becomes OFF when the input voltage (V_{IN}) rises above the release voltage (V_{REL}), and the P-Ch transistor becomes ON. And, the output voltage (V_{OUT}) is equal to input voltage (V_{IN}). This difference between V_{DET} and V_{REL} is hysteresis range (V_{HYS}).

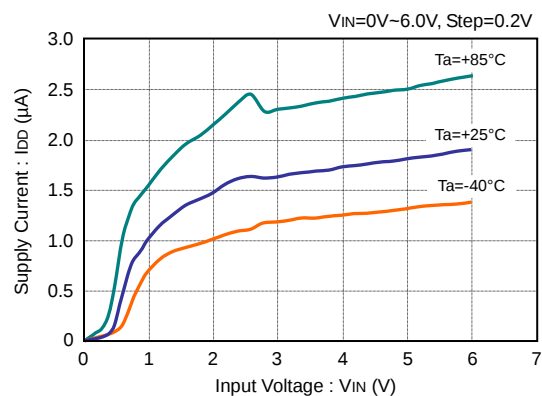


TYPICAL CHARACTERISTICS – Supply Current vs. Input Voltage

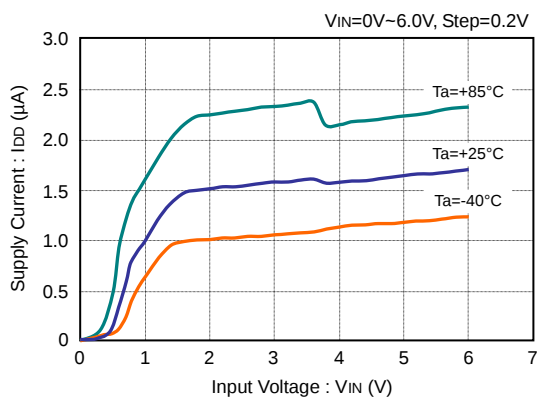
● VDD181SCTA (CMOS 1.8V)



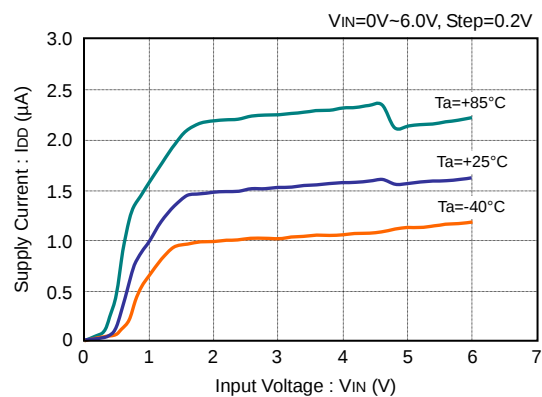
● VDD251SCTA (CMOS 2.5V)



● VDD351SCTA (CMOS 3.5V)

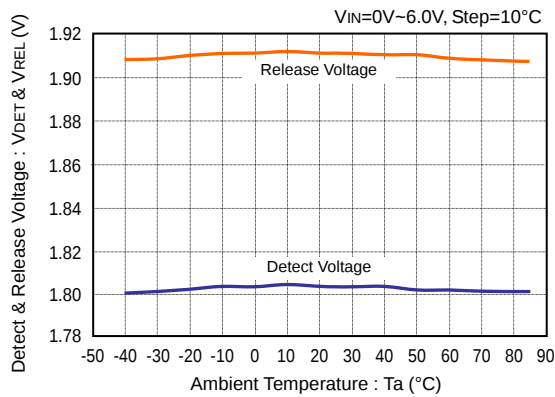


● VDD451SCTA (CMOS 4.5V)

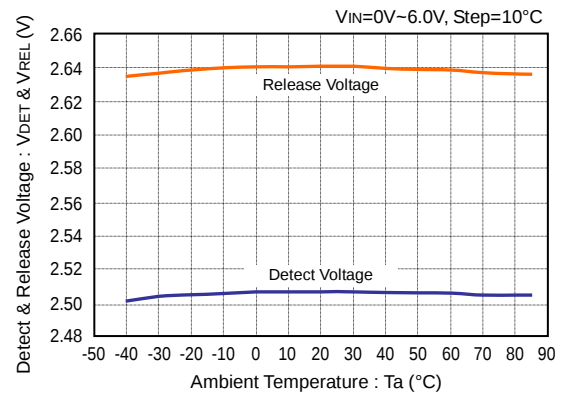


TYPICAL CHARACTERISTICS – Detect & Release Voltage vs. Ambient Temperature

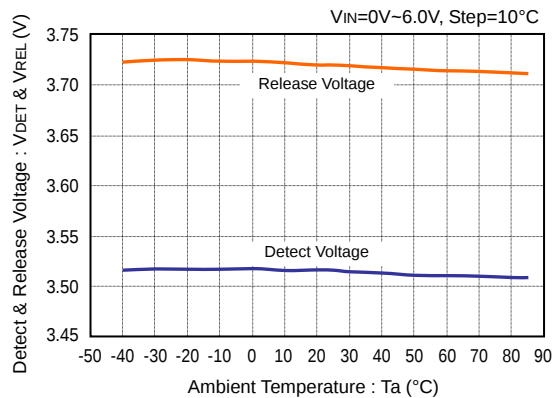
● VDD181SCTA (CMOS 1.8V)



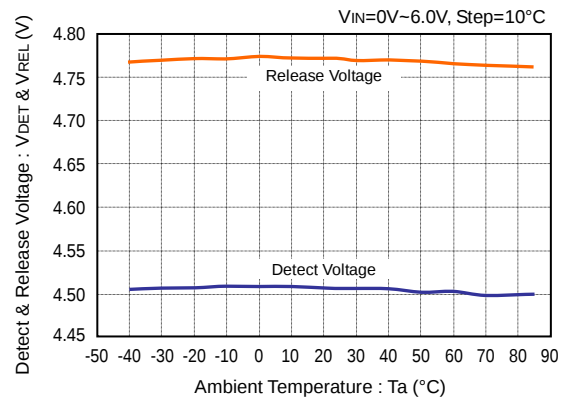
● VDD251SCTA (CMOS 2.5V)



● VDD351SCTA (CMOS 3.5V)

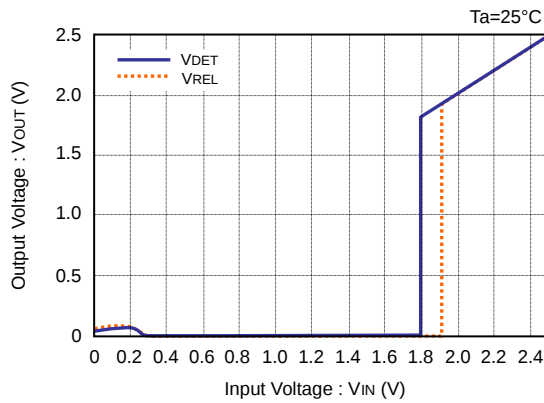


● VDD451SCTA (CMOS 4.5V)

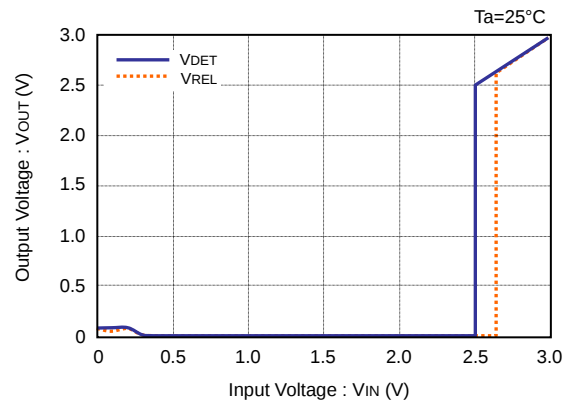


TYPICAL CHARACTERISTICS – Output Voltage vs. Input Voltage

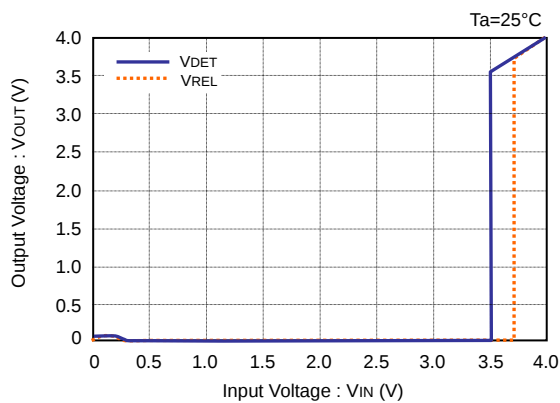
● VDD181SCTA (CMOS 1.8V)



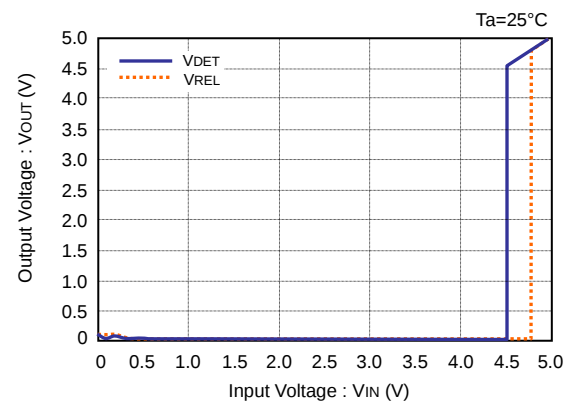
● VDD251SCTA (CMOS 2.5V)



● VDD351SCTA (CMOS 3.5V)

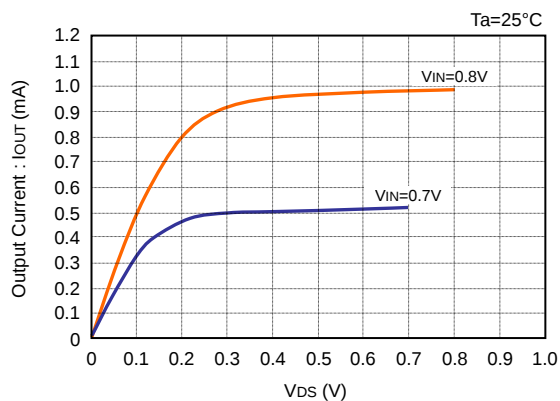


● VDD451SCTA (CMOS 4.5V)

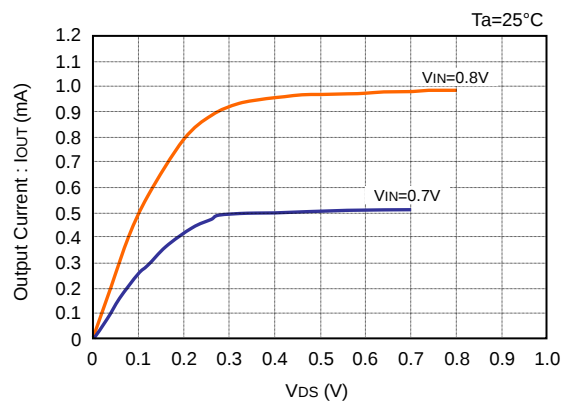


TYPICAL CHARACTERISTICS – N-ch Driver Output Current vs. V_{DS}

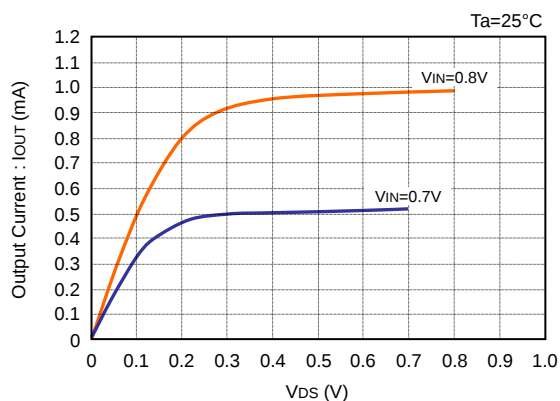
● VDD181SCTA (CMOS 1.8V)



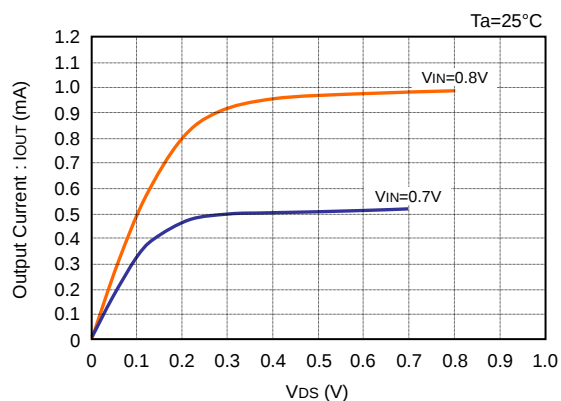
● VDD251SCTA (CMOS 2.5V)



● VDD351SCTA (CMOS 3.5V)

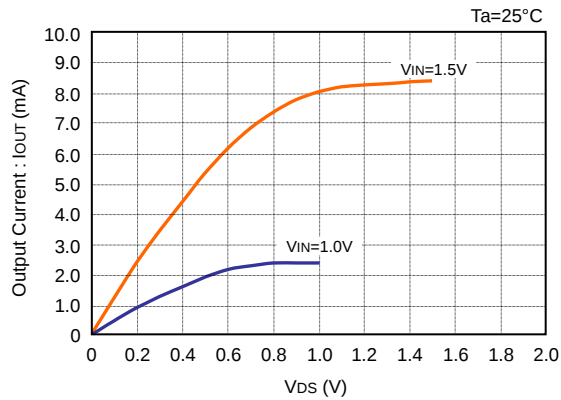


● VDD451MCTA (CMOS 4.5V)

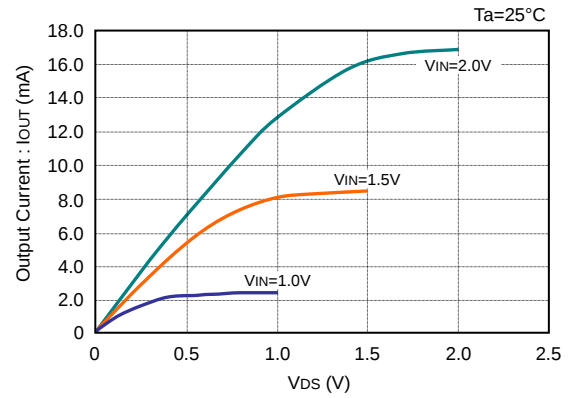


TYPICAL CHARACTERISTICS – N-ch Driver Output Current vs. V_{DS} (continued)

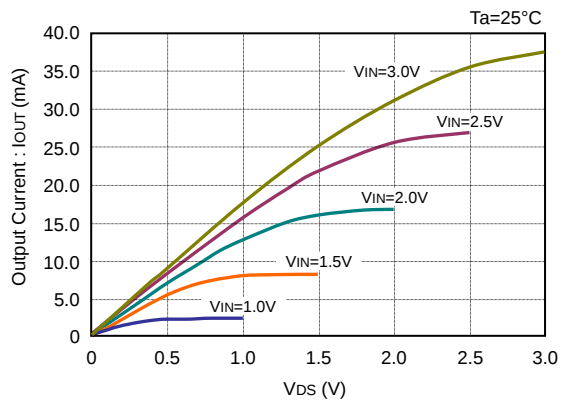
● VDD181SCTA (CMOS 1.8V)



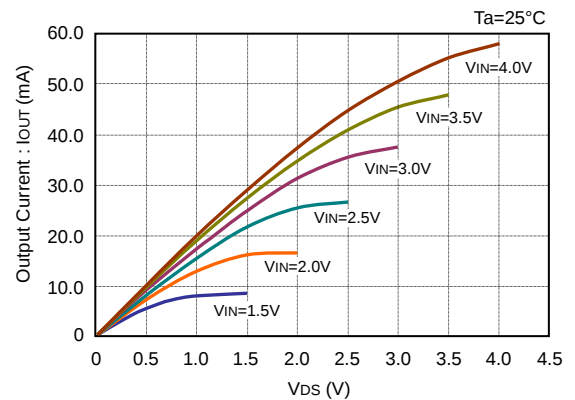
● VDD251SCTA (CMOS 2.5V)



● VDD351SCTA (CMOS 3.5V)

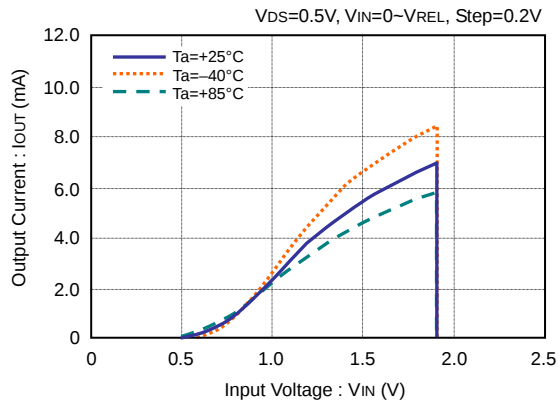


● VDD451MCTA (CMOS 4.5V)

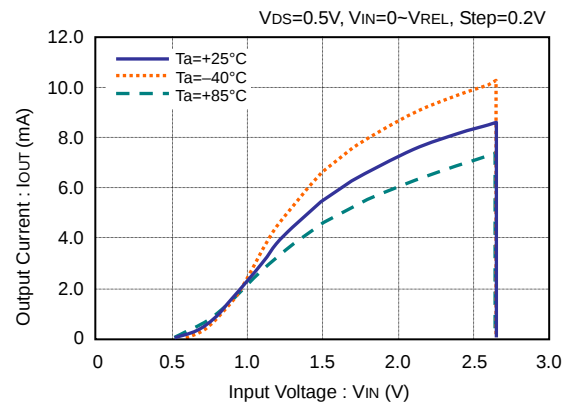


TYPICAL CHARACTERISTICS – N-ch Driver Output Current vs. Input Voltage

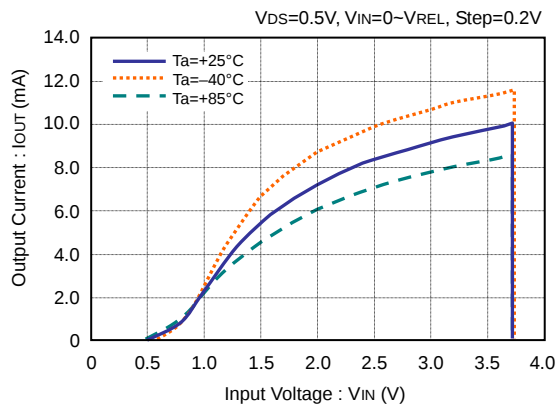
● VDD181SCTA (CMOS 1.8V)



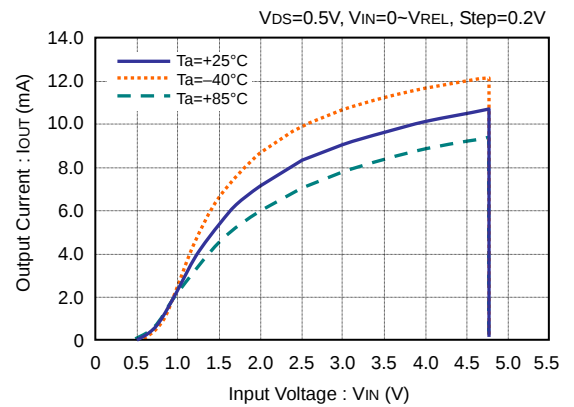
● VDD251SCTA (CMOS 2.5V)



● VDD351SCTA (CMOS 3.5V)

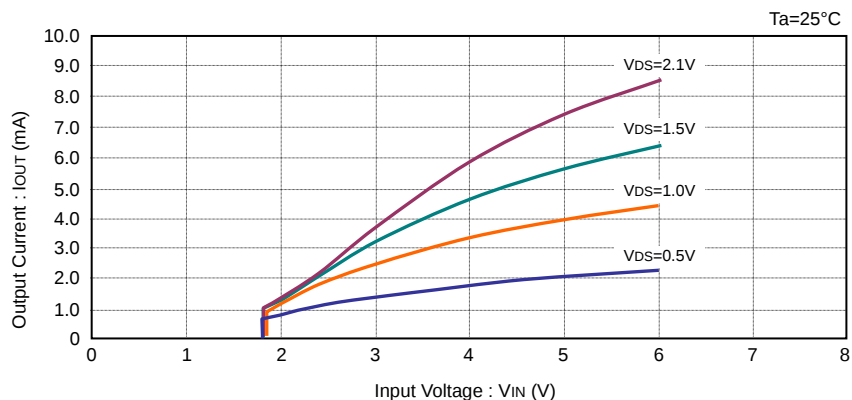


● VDD451SCTA (CMOS 4.5V)

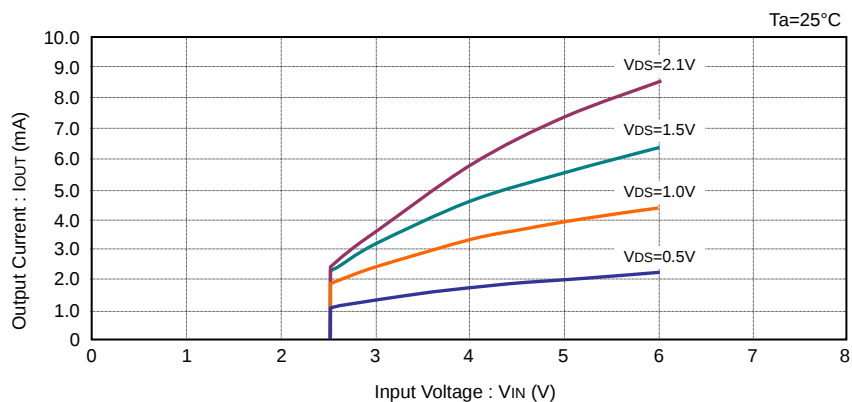


TYPICAL CHARACTERISTICS – P-ch Driver Output Current vs. Input Voltage

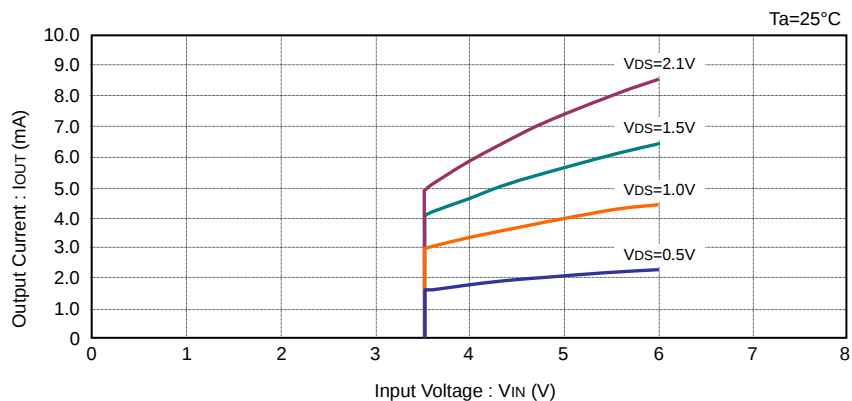
● VDD181SCTA (CMOS 1.8V)



● VDD251SCTA (CMOS 2.5V)

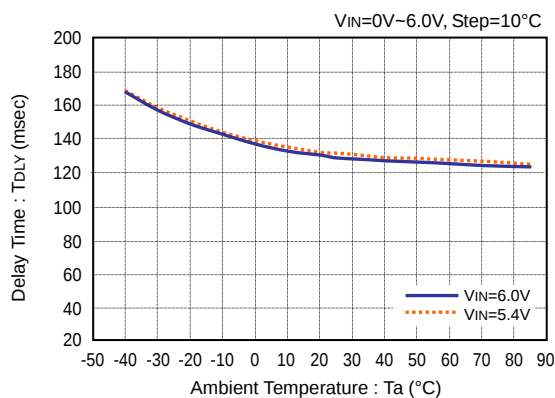


● VDD351SCTA (CMOS 3.5V)

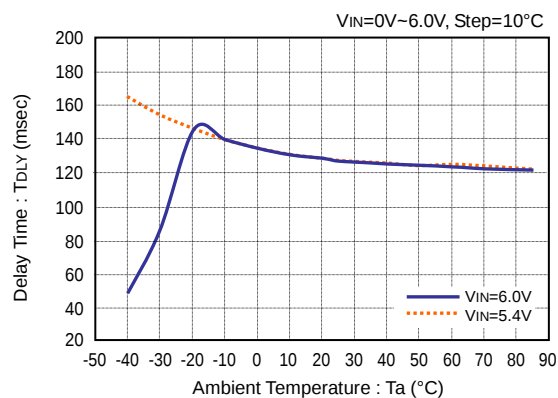


TYPICAL CHARACTERISTICS – Delay Time vs. Ambient Temperature

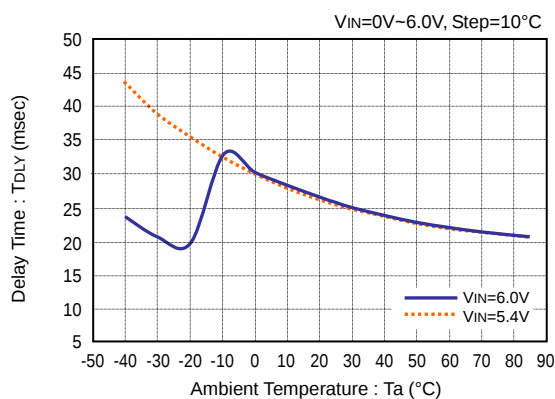
● VDD221MCTA (CMOS 2.2V)



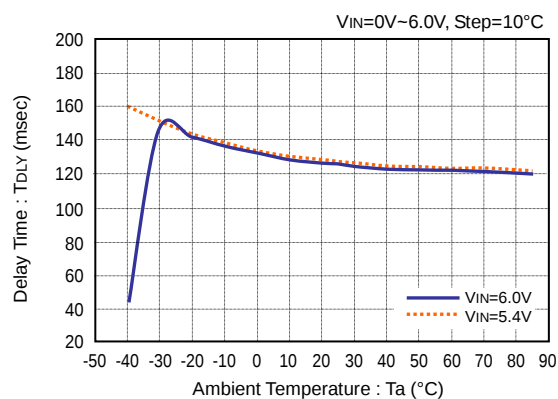
● VDD271MCTA (CMOS 2.7V)

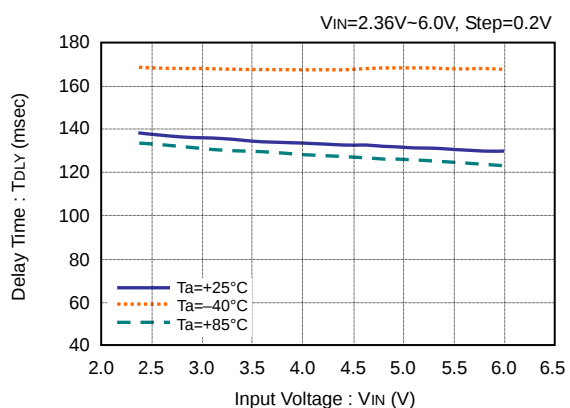
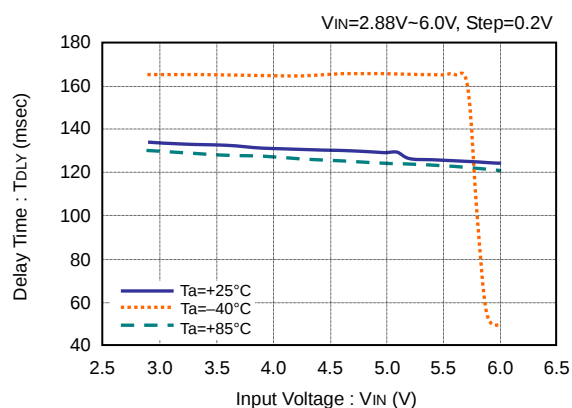
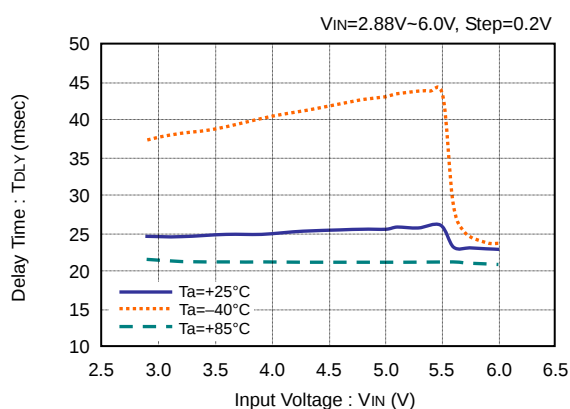
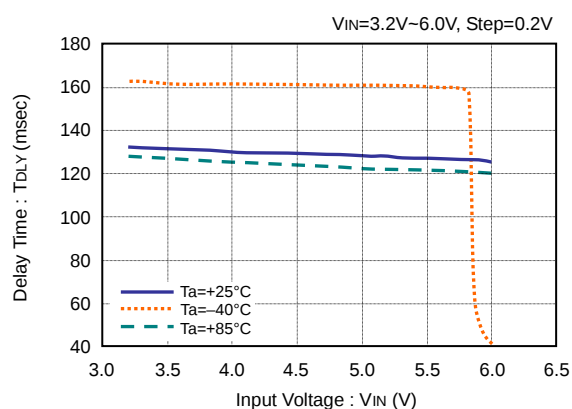


● VDD271SNTA (N-ch 2.7V)

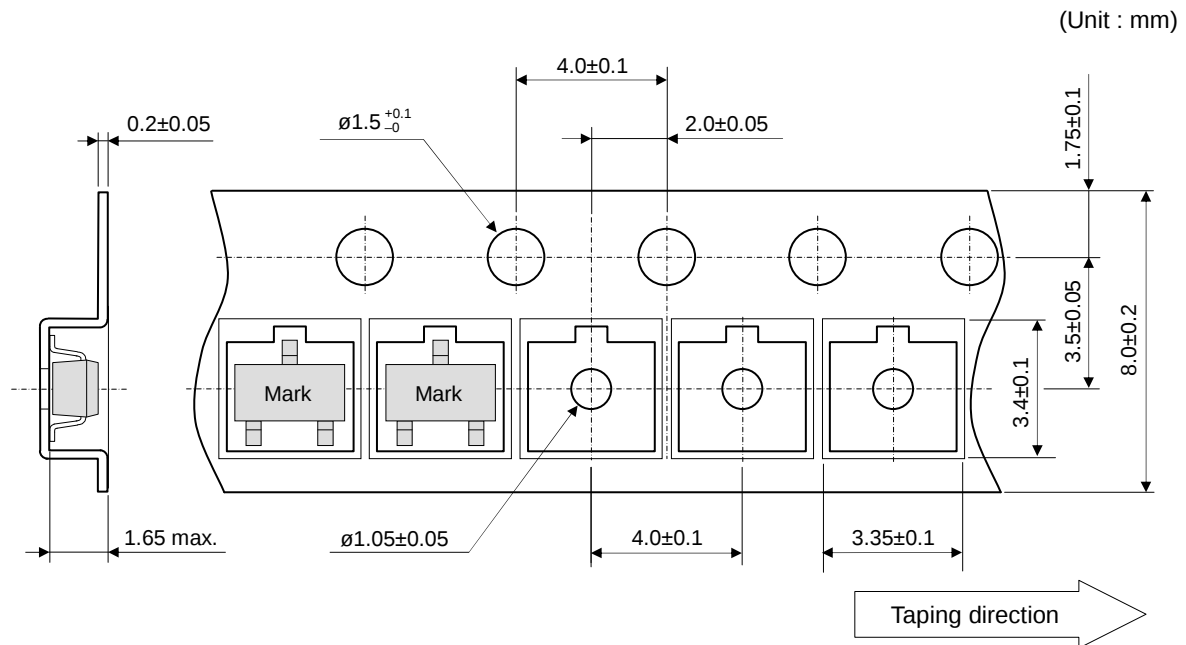


● VDD301MCTA (CMOS 3.0V)

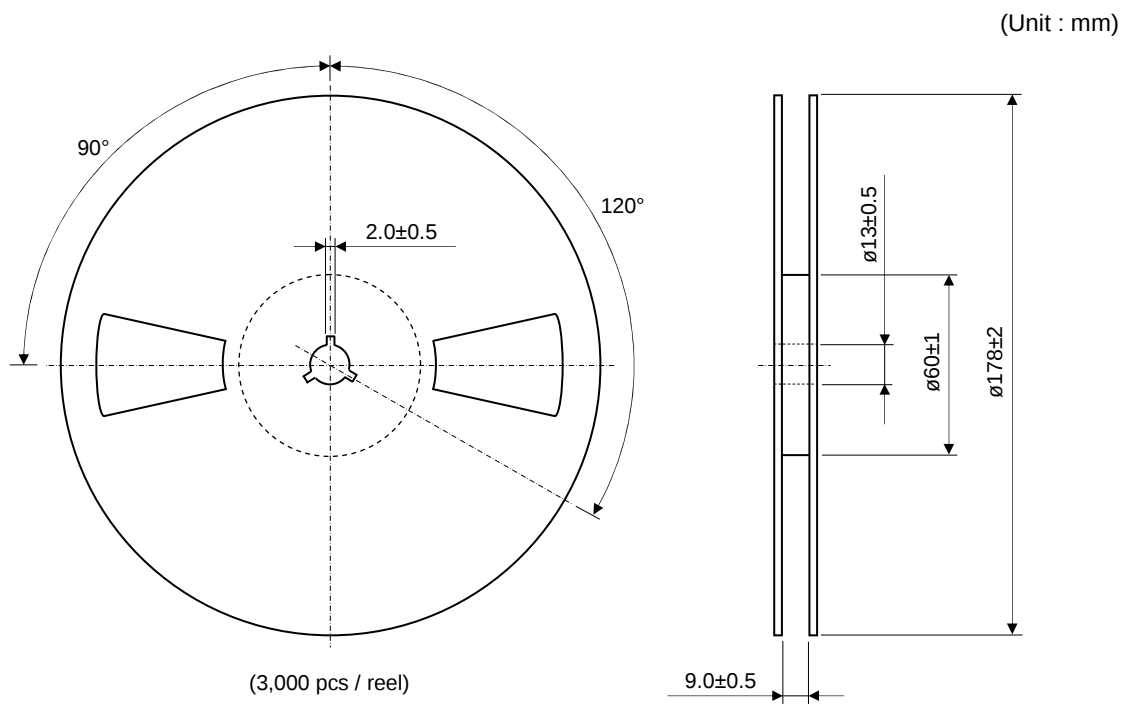


TYPICAL CHARACTERISTICS – Delay Time vs. Input Voltage● **VDD221MCTA (CMOS 2.2V)**● **VDD271MCTA (CMOS 2.7V)**● **VDD271SNTA (N-ch 2.7V)**● **VDD301MCTA (CMOS 3.0V)**

TAPING AND LOADING SPECIFICATIONS (SOT-23)



REEL DIMENSIONS (SOT-23)





AnaSem may change the products described in this data sheet, or may discontinue production or services without any notice in order to supply the best products through improve the design and performance. Customers are recommended to obtain the latest data or information before placing orders in order to make sure the data or information required is the newest. It is necessary for customers to fully understand the products described in this data sheet and to use it in accordance with its specifications. The products described in this data sheet are not intended to use for the apparatus which have influence on human lives due to the failure or malfunction of the products. AnaSem Corp. is not responsible for any support to customer's application, product design, software performance, patent infringement or service. AnaSem Corp. does not disclose or imply a guarantee or description about being licensed based on patents, copy-rights, circuit location license, or other intellectual properties associated with the devices or combinations in which the products or service of AnaSem Corp. are used or can be used, or which cover the methods. Customers should not export, directly or indirectly, any products without obtaining required licenses and approvals in advance from appropriate government agencies.

GENUINE PRODUCT LEGITIMATE LABEL DEFINITION

